Ordering number : ENA0785

SANYO Semiconductors
DATA SHEET

N-Channel Silicon MOSFET

SFT1402 — General-Purpose Switching Device Applications

Features

- Motor drive application.
- Low ON-resistance.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		35	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		11	A
Drain Current (PW≤10μs)	I_{DP}	PW≤10μs, duty cycle≤1%	44	A
Allowable Power Dissipation	P_D		1.0	W
		Tc=25°C	15	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	35			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=35V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0V			±10	μA
Cutoff Voltage	$V_{GS}(off)$	V_{DS}=10V, I_D=1mA	1.2		2.6	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=10V, I_D=5.5A	4.6	7.7		S
Static Drain-to-Source On-State Resistance	$R_{DS}(on)1$	I_D=5.5A, V_{GS}=10V		24	32	mΩ
	$R_{DS}(on)2$	I_D=5.5A, V_{GS}=4V		40	56	mΩ

Marking : T1402

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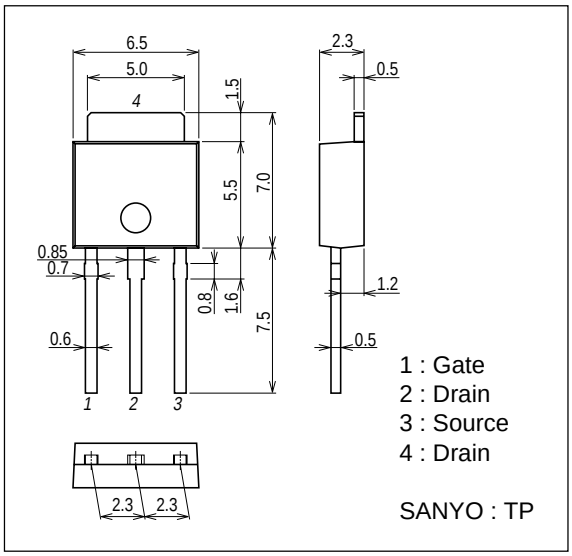
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		1050		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		200		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		140		pF
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit.		14		ns
Rise Time	t_{r}	See specified Test Circuit.		85		ns
Turn-OFF Delay Time	t_{d}(off)	See specified Test Circuit.		70		ns
Fall Time	t_{f}	See specified Test Circuit.		60		ns
Total Gate Charge	Qg	V_{DS}=20V, V_{GS}=10V, I_{D}=11A		20		nC
Gate-to-Source Charge	Qgs	V_{DS}=20V, V_{GS}=10V, I_{D}=11A		4.2		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=20V, V_{GS}=10V, I_{D}=11A		4.0		nC
Diode Forward Voltage	V_{SD}	I_{S}=11A, V_{GS}=0V		0.93	1.2	V

Package Dimensions

unit : mm (typ)

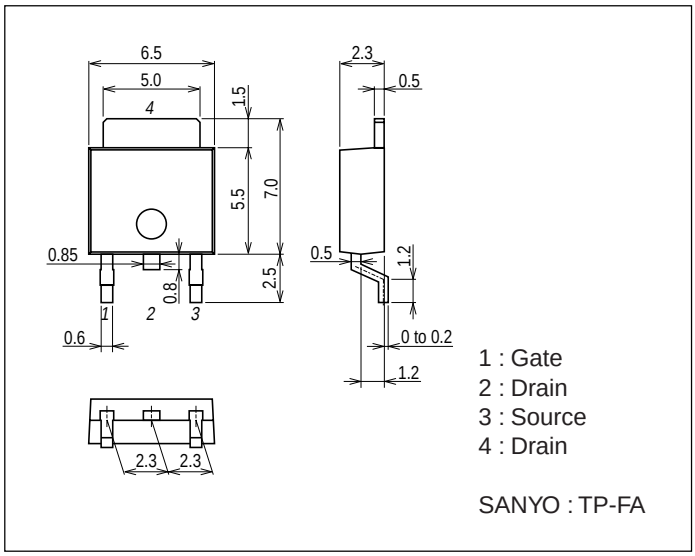
7518-004



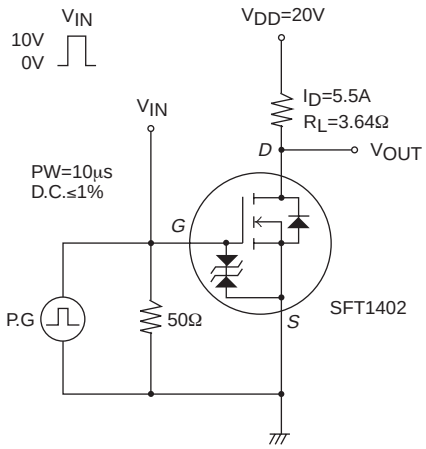
Package Dimensions

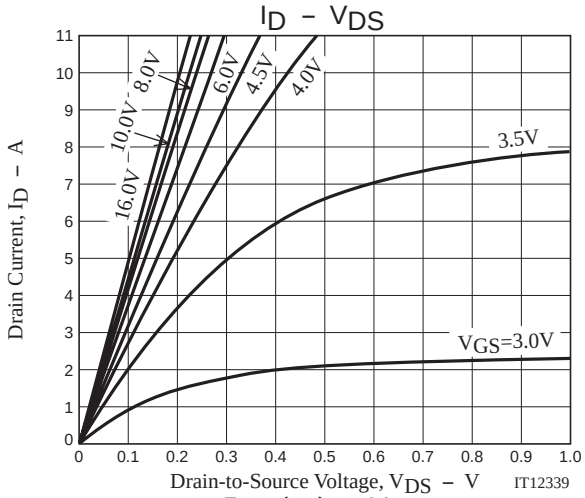
unit : mm(typ)

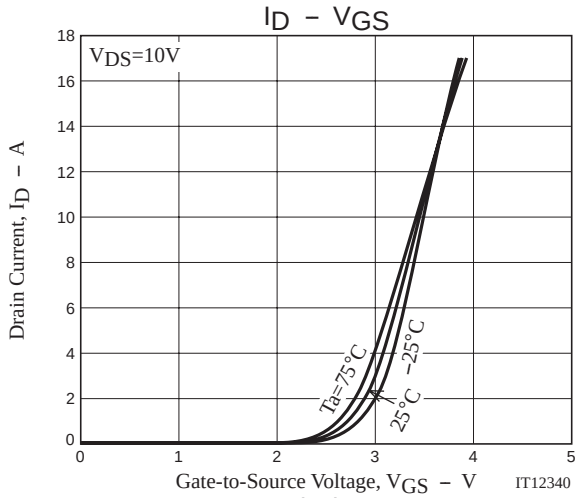
7003-004

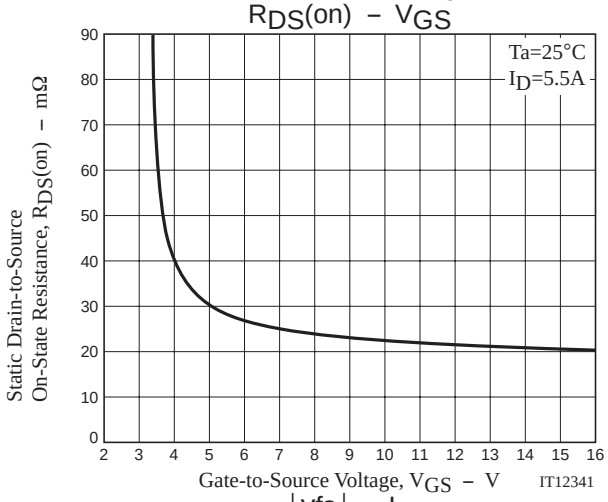


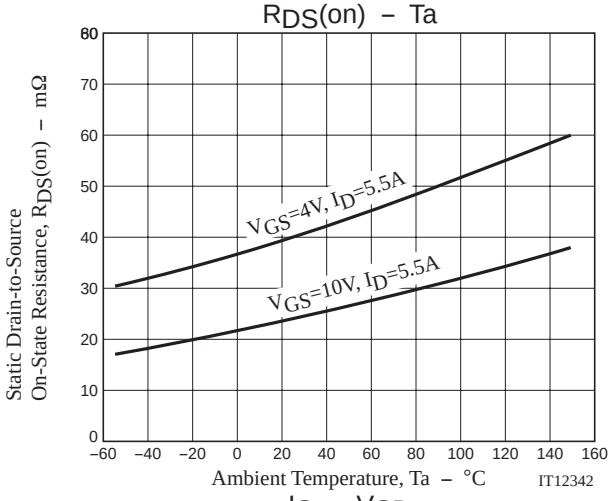
Switching Time Test Circuit

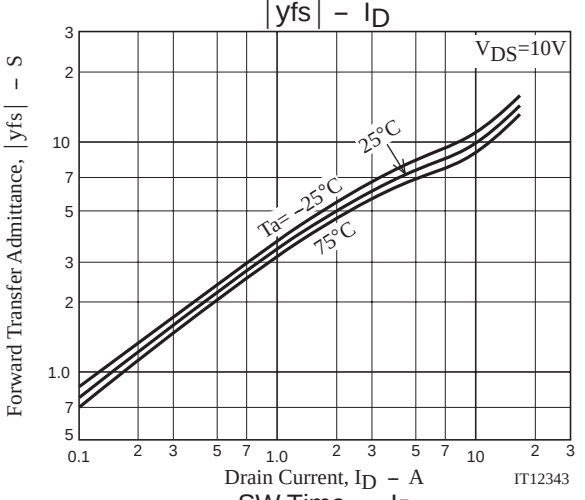


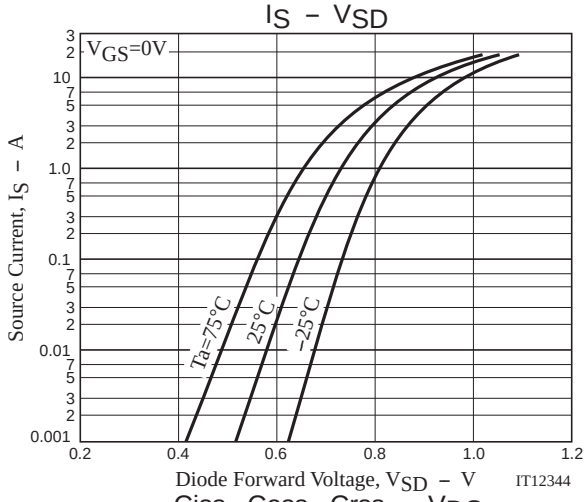

ID – VDS
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT12339
10.0V
8.0V
6.0V
4.5V
4.0V
16.0V
3.5V
VGS=3.0V

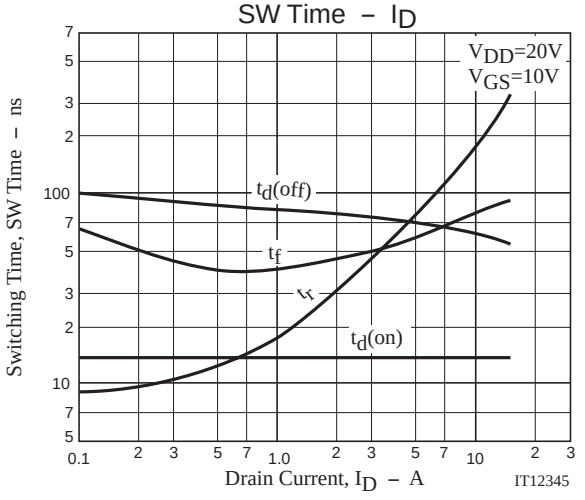

ID – VGS
Drain Current, ID – A
Gate-to-Source Voltage, VGS – V
IT12340
VDS=10V
Ta=75°C
25°C
–25°C

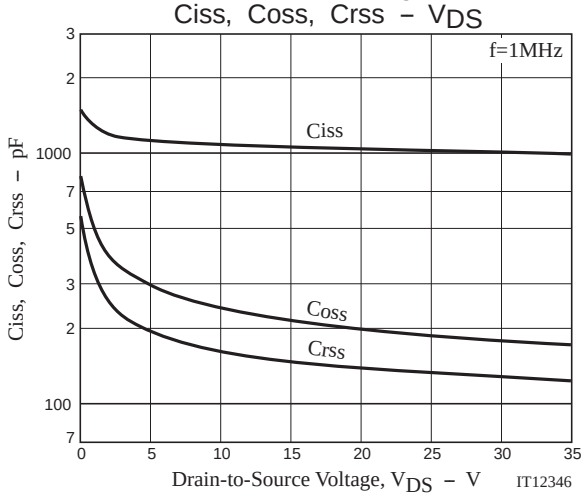

RDS(on) – VGS
Static Drain-to-Source
On-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage, VGS – V
IT12341
Ta=25°C
ID=5.5A

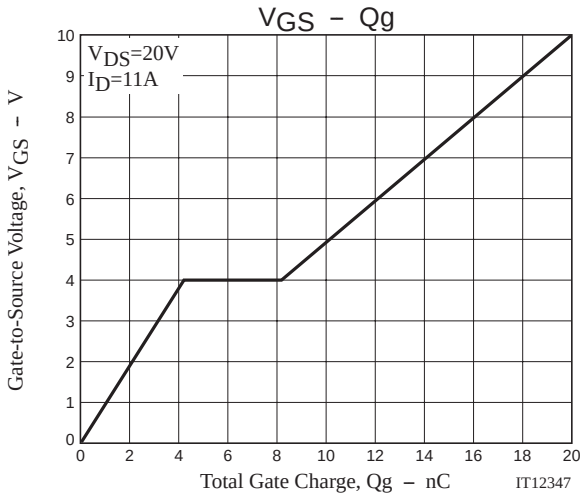

RDS(on) – Ta
Static Drain-to-Source
On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
IT12342
VGS=4V, ID=5.5A
VGS=10V, ID=5.5A

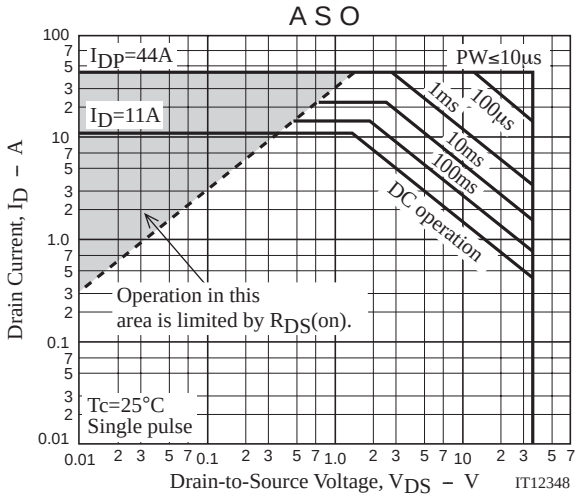

|yfs| – ID
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT12343
VDS=10V
25°C
Ta=–25°C
75°C

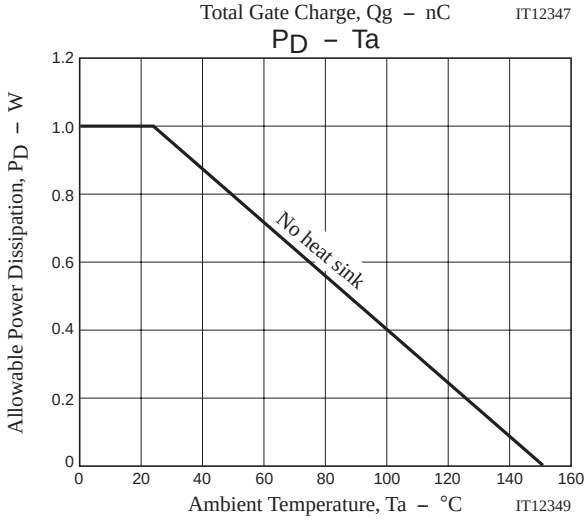

IS – VSD
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT12344
VGS=0V
Ta=75°C
25°C
–25°C

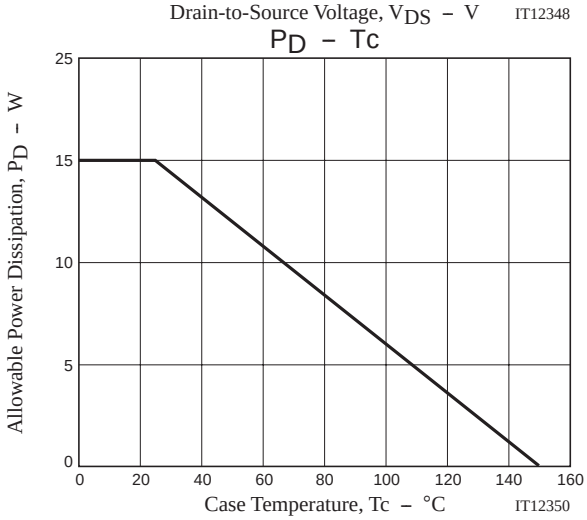

SW Time – ID
Switching Time, SW Time – ns
Drain Current, ID – A
IT12345
VDD=20V
VGS=10V
td(off)
tf
tr
td(on)


Ciss, Coss, Crss – VDS
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT12346
f=1MHz
Ciss
Coss
Crss









Note on usage : Since the SFT1402 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.